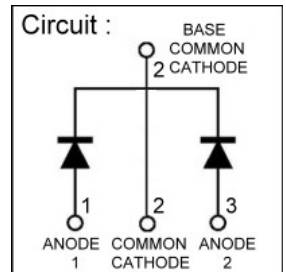
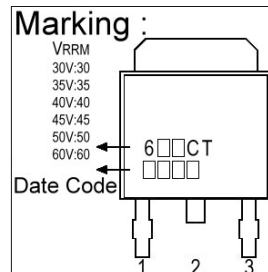
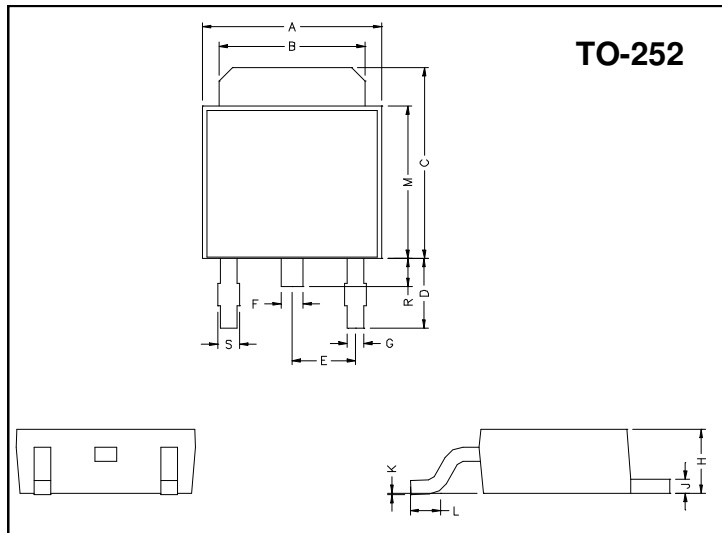


GJSBL630CT~660CT**SCHOTTKY BARRIER RECTIFIERS****REVERSE VOLTAGE 30V TO 60V, CURRENT 6 A****Description**

The GJSBL630CT~660CT are designed for use in low voltage, high frequency inverters, free wheeling and polarity protection applications.

Features

- Guard ring for transient protection
- Low power loss, high efficiency
- High current capability, low V_F
- High surge capacity

Package Dimensions

REF.	Millimeter		REF.	Millimeter	
	Min.	Max.		Min.	Max.
A	6.40	6.80	G	0.50	0.70
B	5.20	5.50	H	2.20	2.40
C	6.80	7.20	J	0.45	0.55
D	2.40	3.00	K	0	0.15
E	2.30 REF.		L	0.90	1.50
F	0.70	0.90	M	5.40	5.80
S	0.60	0.90	R	0.80	1.20

Maximum Ratings and Electrical Characteristics at $T_a=25^\circ\text{C}$ unless otherwise specified.

Single phase, half wave, 60Hz, resistive or inductive load. For capacitive load, derate current by 20%

Parameters	Symbol	Ratings						Unit
		GJSBL 630CT	GJSBL 635CT	GJSBL 640CT	GJSBL 645CT	GJSBL 650CT	GJSBL 660CT	V
Max. Recurrent Peak Reverse Voltage	V _{RRM}	30	35	40	45	50	60	V
Max. RMS Voltage	V _{RMS}	21	24.5	28	31.5	35	42	V
Max. DC Blocking Voltage	V _{DC}	30	35	40	45	50	60	V
Max. Average Forward Rectified Current (See Fig.1) @T _C =95°C	I _(AV)	6						A
Peak Surge Forward Current 8.3ms single half sine-wave superimposed on rated load (JEDEC METHOD)	I _{FSM}	75						A
Max. Forward Voltage @ 3A (Note 1)	V _F	0.55				0.7		V
Max. DC Reverse Current @T _J =25°C At Rated DC Blocking Voltage @T _J =100°C	I _R	0.5 50						mA
Typical Thermal Resistance @T _C =25°C (Note2)	R _{θJC}	20						°C/W
Operating Temperature Range	T _j	-55 ~ +125						°C
Storage Temperature Range	T _{stg}	-55 ~ +150						°C

Notes: 1. 300us Pulse Width, 2% Duty Cycle.

2. Thermal Resistance Junction to Case.

Characteristics Curve

Fig. 1 Forward Current Derating Curve

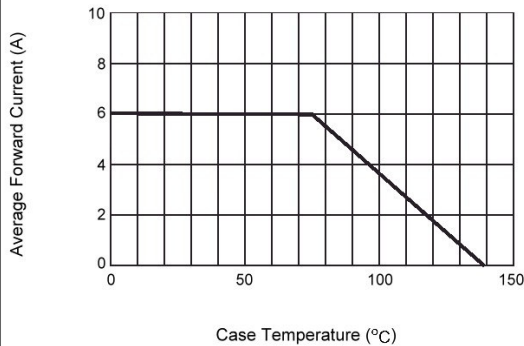


Fig. 2 Maximum Non-Repetitive Surge Current

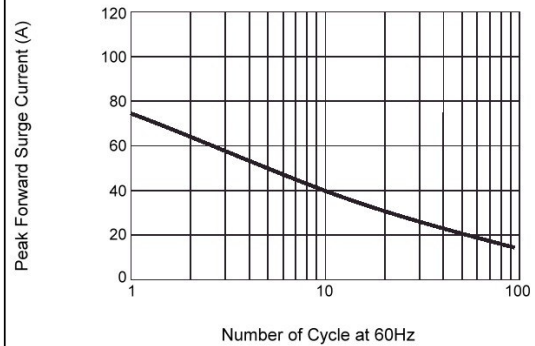


Fig. 3 Typical Reverse Characteristics

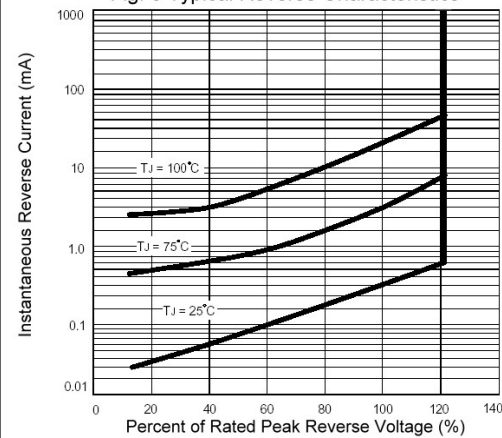


Fig. 4 Typical Instantaneous Forward Characteristic

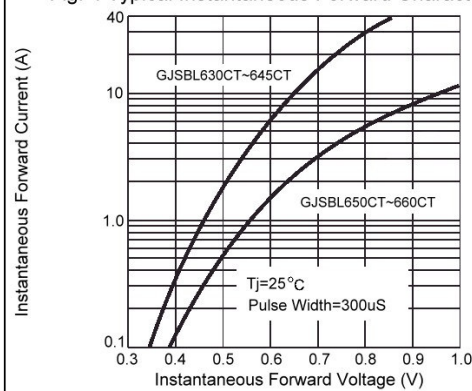
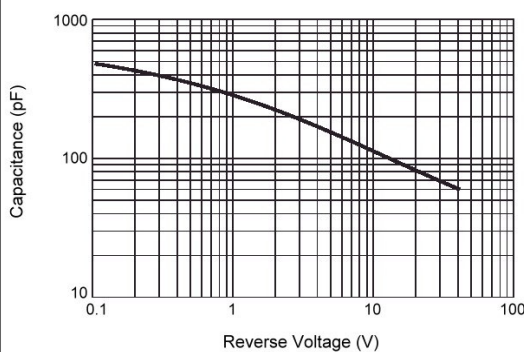


Fig. 5 Typical Junction capacitance



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